

First principles study of heavily doped full Heusler Fe_2YZ for high thermoelectric power factor

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Introduction

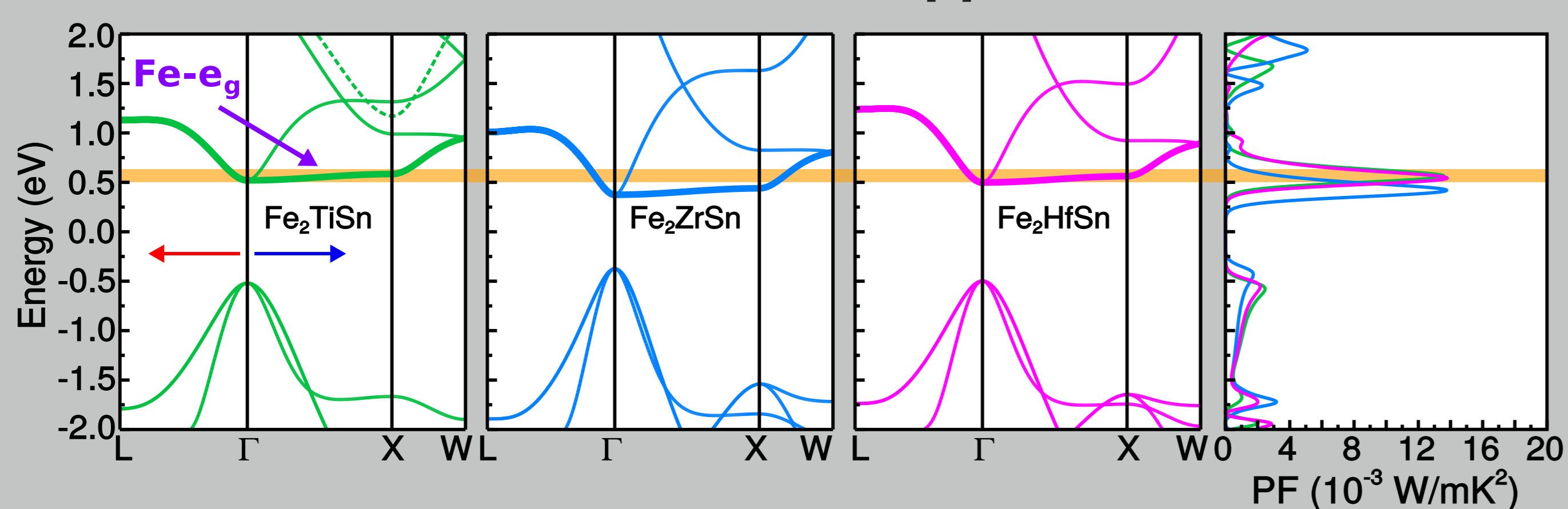
- The performance of thermoelectric materials is characterized by the Figure of Merit ZT , related to the Carnot efficiency:

$$ZT = \frac{S^2\sigma}{\kappa_l + \kappa_e} T \quad \eta = \eta_{\text{Carnot}} \frac{\sqrt{ZT + 1} - 1}{\sqrt{ZT + 1} + 1}$$

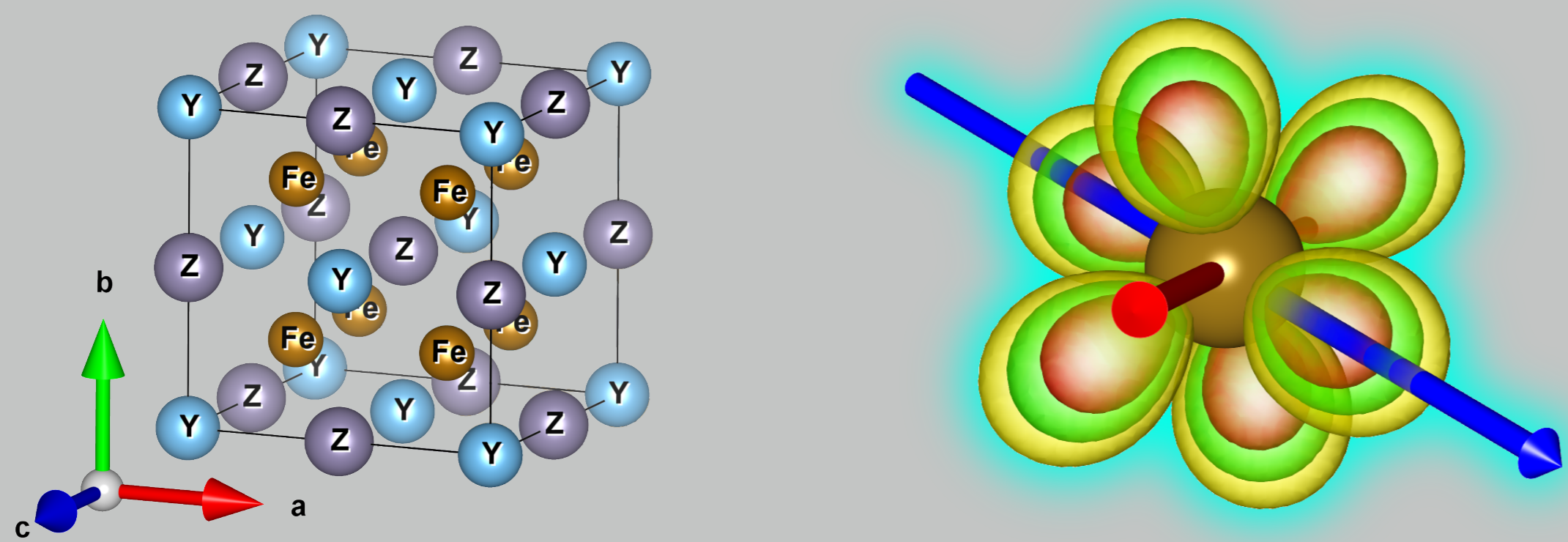
- The Power Factor $S^2\sigma$ is the key quantity to optimize for practical applications, such as heat waste recovery.
- S requires **low** effective mass carriers, σ requires **high** effective mass carriers.

$$m_{\alpha\beta}^* = \left[\frac{1}{\hbar^2} \frac{\partial^2 \epsilon(\mathbf{i}, \mathbf{k})}{\partial k_\alpha \partial k_\beta} \right]^{-1}$$

- Both characters can be met in a single band from orbitals with highly directional characters \rightarrow **HIGH** Power Factor !
- Where can we find such a band ? In Fe_2YZ semiconductors, bottom of the conduction band ! Extensive work from Ref. [1] \rightarrow Promising **bulk TE** !



- Fe_2YZ compounds presents $\text{Fe} - e_g$ orbitals, main contribution to the bottom of the conduction band with the aforementioned features.

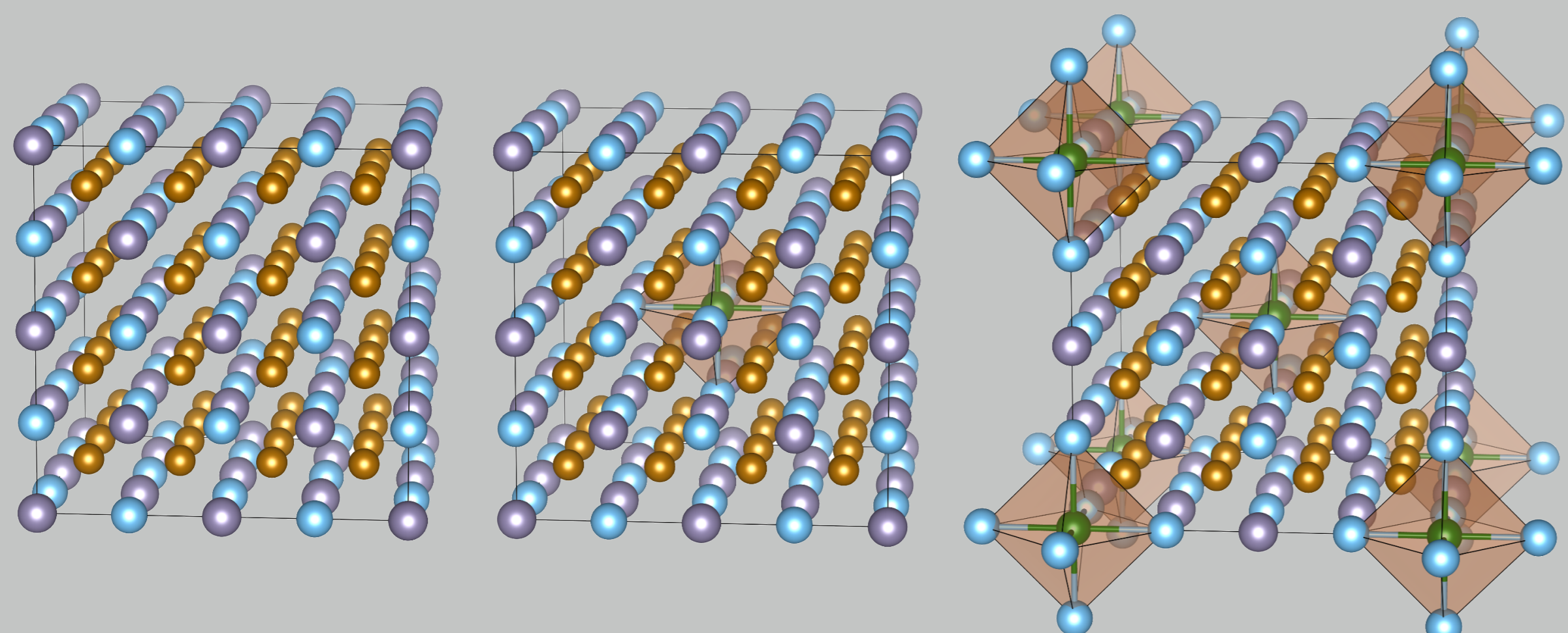


- In the rigid band approx., n -type doping from $0.2 \times 10^{21} \text{ cm}^{-3}$ to $1.0 \times 10^{21} \text{ cm}^{-3}$ shift the Fermi level to the flat part of the $\text{Fe} - e_g$ band, ensuring maximum $S^2\sigma$.

Technical details

- Doping simulated by the $2 \times 2 \times 2$ cubic supercell method: 128 atoms, 1 or 2 Y atoms replaced by A $\rightarrow \sim 0.6 \times 10^{21} \text{ cm}^{-3}$ and $\sim 1.2 \times 10^{21} \text{ cm}^{-3}$ n -type doping values. The following compounds are studied :

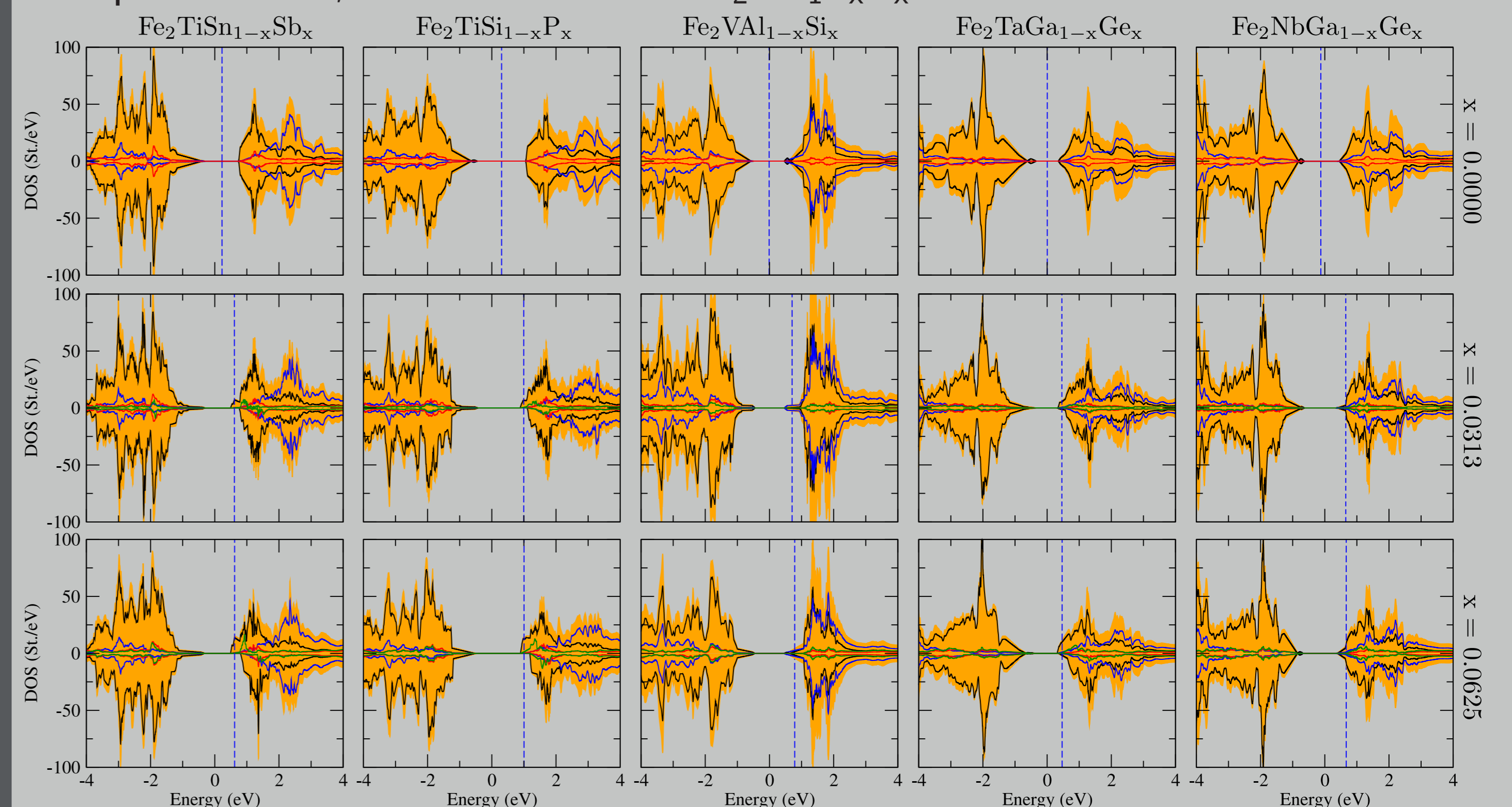
- $\text{Fe}_2\text{TiSn}_{1-x}\text{Sb}_x$;
- $\text{Fe}_2\text{TiSi}_{1-x}\text{P}_x$;
- $\text{Fe}_2\text{VAI}_{1-x}\text{Si}_x$;
- $\text{Fe}_2\text{TaGa}_{1-x}\text{Ge}_x$;
- $\text{Fe}_2\text{NbGa}_{1-x}\text{Ge}_x$; each with $x = 0.0000; 0.0313; 0.0625$.



- Crystal14 package for the DFT calculations [2, 3], with **B1 Wu-Cohen** hybrid functional for E_{xc} .
- Thermoelectric properties computed with BoltzTraP [4]
- $9 \times 9 \times 9$ Monkhorst-Pack k -mesh for structural relaxation of conv. cell. (lattice para. + atomic positions).
- $5 \times 5 \times 5$ Monkhorst-Pack k -mesh for structural relaxation of SC (lattice para. + atomic positions).
- $10 \times 10 \times 10$ Monkhorst-Pack k -mesh for electronic properties.
- $32 \times 32 \times 32$ Monkhorst-Pack k -mesh for transport and TE properties.
- Energy convergence criterium fixed at 10^{-9} Ha.
- Relaxation time $\tau = 3.4 \times 10^{-14}$ s, from ref. [1].
- Basis sets, same as Ref. [1].

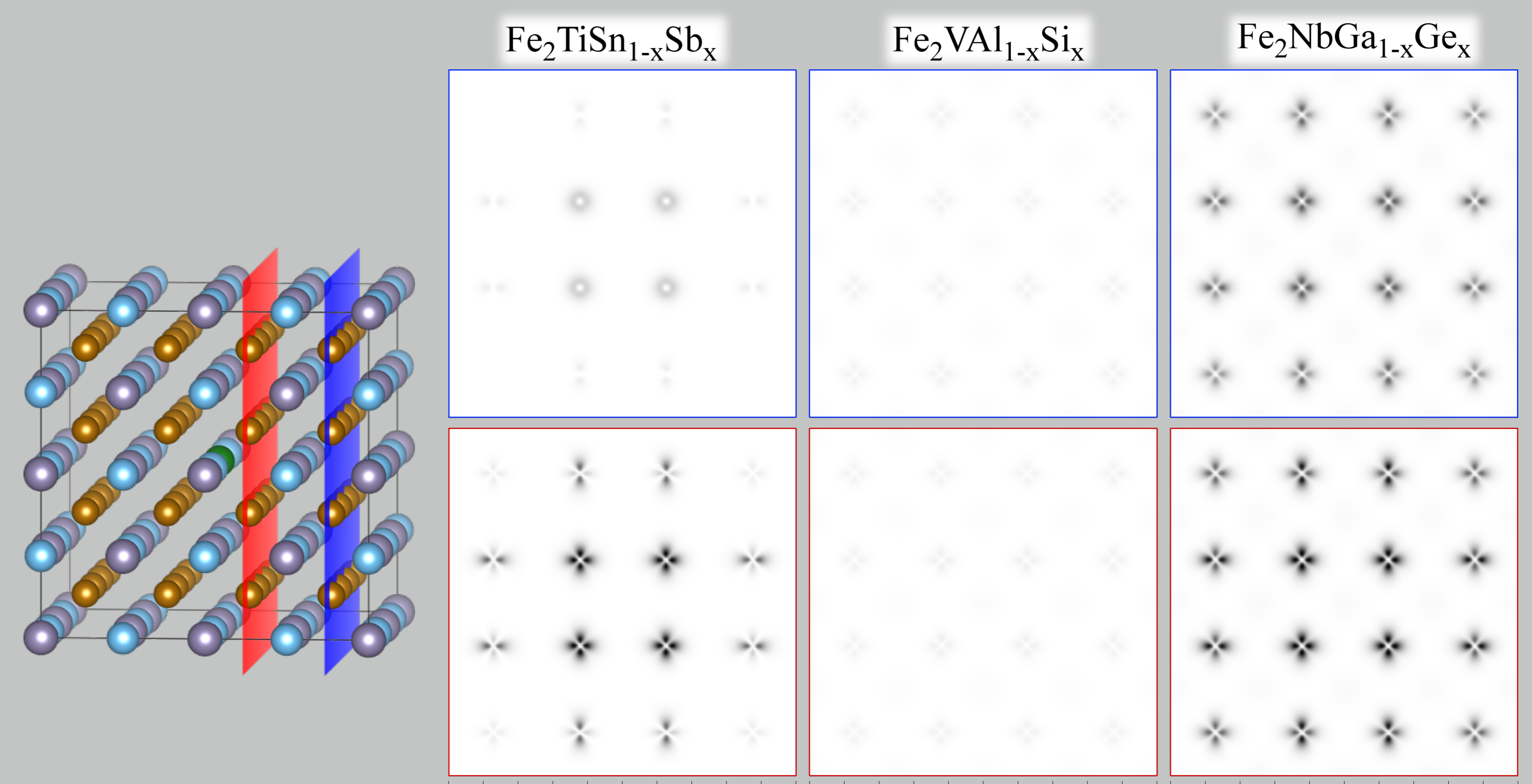
Electronic properties

- Spin-resolved, atomic PDOS of $\text{Fe}_2\text{YZ}_{1-x}\text{A}_x$:



- Depending the matrix, **half-metallic** and **metallic** phases appear, previously associated with disorder [5].

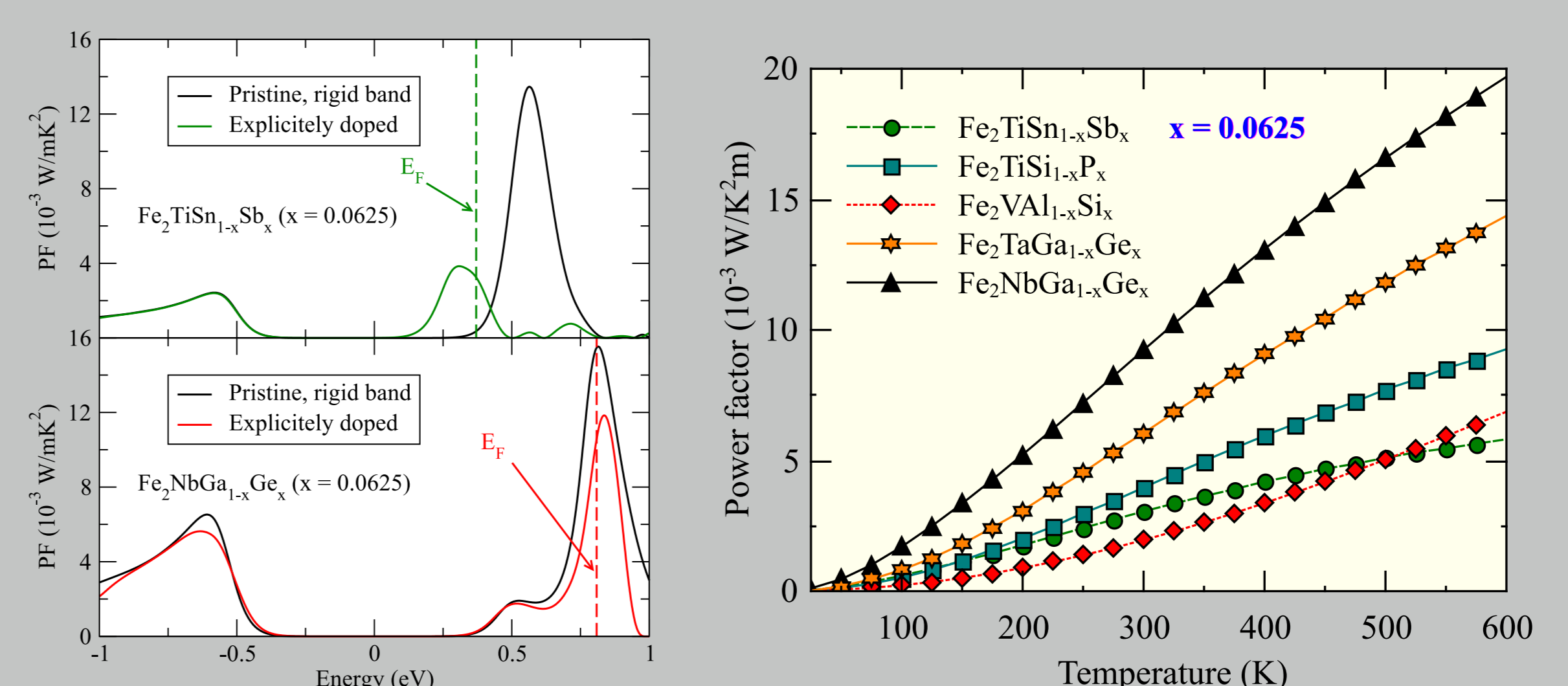
- Electron density of the excess charge ($x = 0.0313$):



- Results consistent with a **Stoner instability** studied through a Jellium model (fixed geometry + $1 e^-$ + charged background): $\Delta E_{ex} \times g^{NM}(E_F) > 1$

X_2YZ	ΔE_{ex} [eV]	$g^{NM}(E_F)$ [St./eV]	$\Delta E_{ex} \times g^{NM}(E_F)$
Fe_2TiSn	0.200	35.31	7.1
Fe_2TiSi	0.154	37.84	5.8
Fe_2VAI	0.000	8.07	0.0
Fe_2TaGa	0.097	25.14	2.4
Fe_2NbGa	0.060	13.76	0.8

Thermoelectric properties



Despite spin-splitting a wide array of good **PF** can be achieved.

Conclusions

- n -type doping shifts the Fermi level toward the $\text{Fe} - e_g$ band.
- Spin-splitting of the $\text{Fe} - e_g$ band occurs in $\text{Fe}_2\text{TiSn}_{1-x}\text{Sb}_x$, $\text{Fe}_2\text{TiSi}_{1-x}\text{P}_x$, and $\text{Fe}_2\text{TaGa}_{1-x}\text{Ge}_x$.
- A **wide array of good power factors** can be achieved at higher temperatures, ranging from 5 to $20 \times 10^{-3} \text{ W/K}^2\text{m}$.
- n -type doped Fe_2NbGa is the most promising candidate !

References

- [1] D. I. Bilc, et al. *Phys. Rev. Letters*, vol. 114, p. 136601, Mar 2015.
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- [5] A. Jezierski and A. Ślębarski, "Atomic disorder and magnetism in Fe_2TiSn alloys," *Journal of Magnetism and Magnetic Materials*, vol. 223, p. 33, 2001.

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